

REMARKS

Claims 1, 4, 8, 9, and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142). Claims 2 and 3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Ozaki et al. (6,402,302). Claims 5-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Device Electronics for Integrated Circuits (Muller). Claims 10 and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Leban (EP 317 171).

15

1. Rejection of claims 1, 4, 8, 9, and 12 under 35 U.S.C. 103(a):

Claims 1, 4, 8, 9, and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) for reasons of record, as recited on pages 2-3 of the above-indicated Office action.

20

Response:

Claim 1 is currently amended to patentably distinguish from the prior art. The amended claim 1 contains a limitation stating, "at least one layer of the functional device is formed on the same poly-silicon layer as the first conductive trace".

25

This amendment is supported in paragraph [0035] of the specification. The specification teaches that, "The poly-silicon lines 23 and the gate 64 can be formed in a photo-etching process (PEP) to simplify the manufacturing

30

process." In addition, paragraph [0022] of the specification states that, "Not counting the resistance layers, only one single poly-silicon layer and one single metal layer (SPSM) process is performed in the present invention." These two statements teach that the gate 64 of the MOSFET 15 and the poly-silicon lines 23 (first conductive layer) are formed on the same poly-silicon layer.

Neither Hawkins nor Fujita teach or suggest forming at least one layer of the functional device on the same poly-silicon layer as the first conductive trace. In addition, there is no motivation found in Hawkins, Fujita, or in the prior art known to one skilled in the art that would suggest forming at least one layer of the functional device on the same poly-silicon layer as the first conductive trace.

For these reasons, the currently amended claim 1 is patentably distinct from the cited prior art. Claims 4, 8, 9, and 12 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 1, 4, 8, 9, and 12 is respectfully requested.

2. Rejection of claims 2 and 3 under 35 U.S.C. 103(a):

Claims 2 and 3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Ozaki et al. (6,402,302) for reasons of record, as recited on pages 3-4 of the above-indicated Office action.

Response:

Claims 2 and 3 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 2 and 3 is requested.

5

3. Rejection of claims 5-7 under 35 U.S.C. 103(a):

Claims 5-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Device Electronics for Integrated Circuits (Muller) for reasons of record, as recited on page 4 of the above-indicated Office action.

10

Response:

Claims 5-7 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 5-7 is requested.

15

4. Rejection of claims 10 and 11 under 35 U.S.C. 103(a):

Claims 10 and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hawkins (4,935,752) in view of Fujita (5,666,142) and further in view of Leban (EP 317 171) for reasons of record, as recited on page 5 of the above-indicated Office action.

20

25 **Response:**

Claims 10 and 11 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 10 and 11 is requested.

30 5. Introduction to new claim 26:

New claim 26 contains a further limitation to more

clearly define the claimed invention. Claim 26 states that the gate of the MOSFET is formed on the same poly-silicon layer as the first conductive trace. This amendment is also supported in paragraph [0035] of the specification. No new
5 matter is added through this limitation. Acceptance of claim 26 is respectfully requested.

6. Amendment of claims 10-12:

Claims 10-12 are amended to make the respective
10 preambles consistent with the preambles of claims 1-9. No new matter is added.

Respectfully submitted,

15

Winston Hsu

Date: *9/14/2004*

Winston Hsu, Patent Agent No.41,526

P.O. BOX 506

20 Merrifield, VA 22116

U.S.A.

e-mail: winstonhsu@naipo.com

(Please contact me by e-mail if you need a telephone
communication and I will return your call promptly.)

25